0039-6348-2SRD REISSUE

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE REISSUE OF U.S. PATENT NO: 5,570,315

PATENTEE: TOMOHARU TANAKA ET AL :

SERIAL NO: 09/134,897 : GROUP ART UNIT: 2824

FILED: AUGUST 17, 1998 : EXAMINER: TRAN

FOR: MULTI-STATE EEPROM HAVING
WRITE-VERIFY CONTROL CIRCUIT

SUPPLEMENTAL AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In responsive to the Official Office Action mailed April 30, 2001, please amend the above-identified application as follows:

IN THE CLAIMS

Supplemental to the Amendment filed Feb. 20, 2001, please further amend the Claims 120, 133, 139 and 150 as shown in the attachment. A complete set of newly amended claims in clean form is shown below.

120. (Amended) A multilevel nonvolatile semiconductor memory device comprising:

a NAND-cell unit including a plurality of memory cells connected in series, each of said memory cells including a transistor with a control gate and a charge storage portion and having storage states of at least three threshold voltage levels;

a plurality of word lines connected to respective control gates;